

## L-Band Radar Transistor

The high power pulsed radar transistor device part number IB1214M300 is designed for L-Band radar systems operating over the instantaneous bandwidth of 1.215-1.400 GHz. While operating in class C mode this common base device supplies a minimum of 300 watts of peak pulse power under the conditions of 100 $\mu$ s pulse width and 10% duty cycle. All devices are 100% screened for large signal RF parameters.



Silicon Bipolar  
– Ultra-high  $f_T$

Class C Operation  
– High Efficiency

Common Base Configuration  
– Single Power Supply

Gold Metal  
– Maximum Reliability

Emitter Ballasting  
– Optimum Thermal Distribution

Internal Impedance Matching  
– Ease of Use  
– Ultra-low Loss Design

BeO Package  
– Unmatched Thermal Reliability

RF Test Fixture  
– Broadband  
– Matched to 50 $\Omega$   
– Long-term Correlation  
– 100% Device RF Screening  
– No External Tuning Allowed

### TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

Lot / SN	Freq (MHz)	Pout (W)	Pin (W)	Ic (A)	RL (dB)	Nc (%)	Gain (dB)	dG (dB)	VSWR 1.5:1	2:1	dlp bin
508513-17	1215	300	30.8	15.00	15	50.0	9.89		S	P	
	1300	300	34.4	14.19	14	52.9	9.41	1.12	S	P	
	1400	300	39.9	13.51	14	55.5	8.76		S	P	-3
508921-1	1215	300	35.7	14.60	14	51.4	9.24		S	P	
	1300	300	39.0	14.21	11	52.8	8.86	0.70	S	P	
	1400	300	42.0	13.46	20	55.7	8.54		S	P	-1

**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	$V_{CES}$	--	75	V	$V_{BE}=0V$ .
BD	Emitter-Base Voltage	$V_{EBO}$	--	2	V	--
BD	Storage Temperature Range	$T_{STG}$	-55	+150	°C	--
BD	Operating Junction Temperature Range	$T_J$	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

**THERMAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.15	°C/W	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ C$ , $P_{OUT}=300W$ .
Note	Screen 'BD' = parameter qualified By Design.					

**PROCESSING SPECIFICATIONS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification.
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071.6, Test Condition C.
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

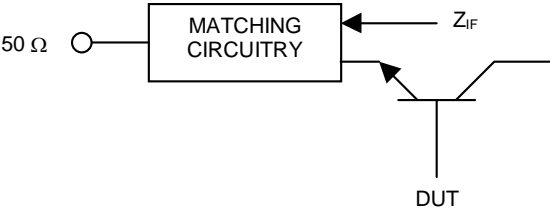
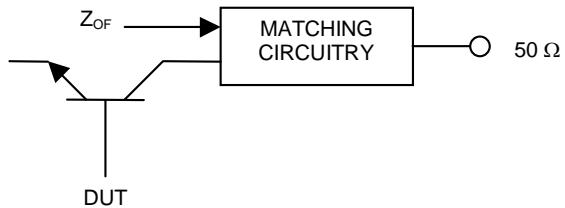
**DC ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	$BV_{CES}$	75	--	V	$I_C=40mA$ , $V_{BE}=0V$ , $T_F=25\pm5^\circ C$ .
100%	Zero Base Voltage Collector Leakage Current	$I_{CES}$	--	10.0	mA	$V_{CE}=40V$ , $V_{BE}=0V$ , $T_F=25\pm5^\circ C$ .
100%	DC Current Gain	$H_{FE}$	20	95	--	$V_{CE}=5V$ , $I_C=0.5A$ , $T_F=25\pm5^\circ C$ .

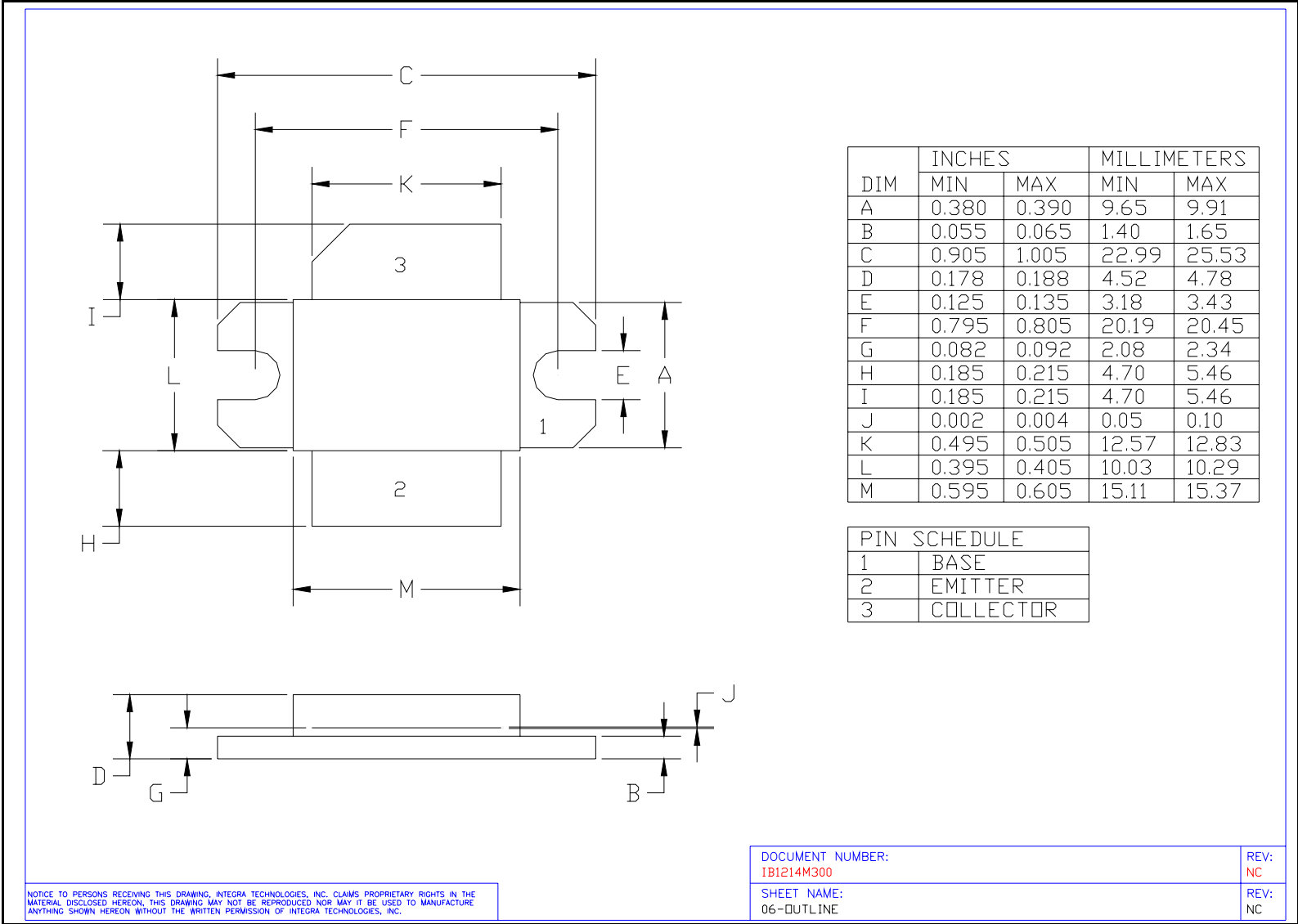
**RF ELECTRICAL CHARACTERISTICS**

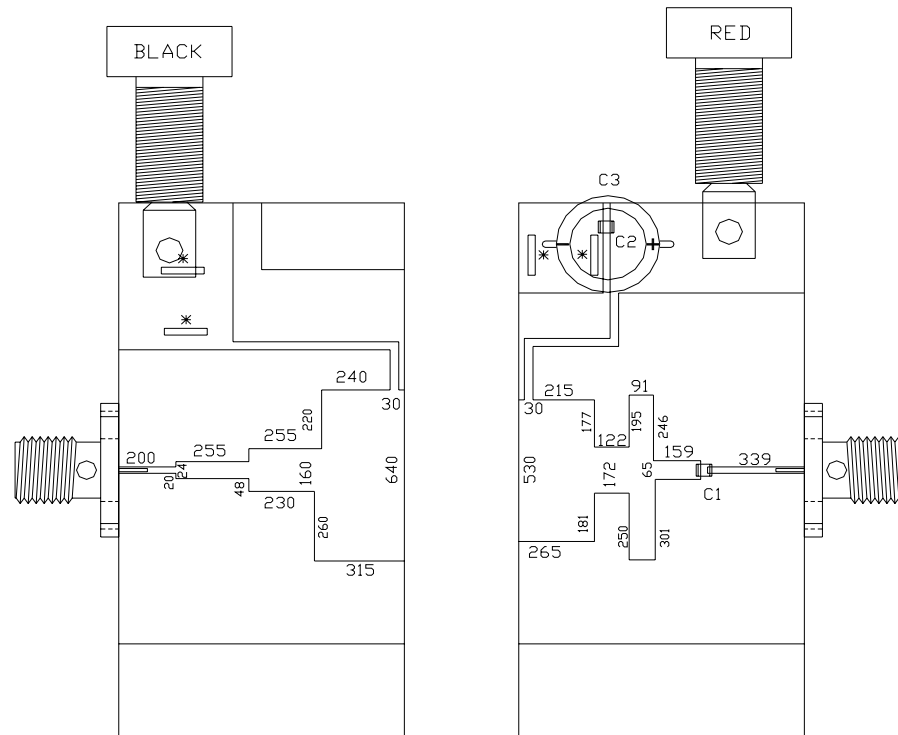
Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	10	--	dB	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT1}$ , $P_{OUT2}$ , $P_{OUT3}$ , $F=F1$ , $F2$ , $F3$ .
100%	Input Power	$P_{IN}$	--	60	W	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT1}$ , $P_{OUT2}$ , $P_{OUT3}$ , $F=F1$ , $F2$ , $F3$ .
100%	Collector Efficiency ( $P_O/I_O/V_{CC}$ )	$N_C$	45	--	%	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT1}$ , $P_{OUT2}$ , $P_{OUT3}$ , $F=F1$ , $F2$ , $F3$ .
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT1}$ , $P_{OUT2}$ , $P_{OUT3}$ , $F=F1$ , $F2$ , $F3$ .
100%	Gain Flatness	GF	--	1.5	dB	Calculate from Gain at each frequency F.
100%	Stability into 1.5:1 VSWR with +0.75dB overdrive	VSWR-S	--	--	--	Repeat $P_O$ with $P_{IN}$ increased by 0.75dB. Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	2:1 Load Mismatch Tolerance	LMT	--	--	--	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT1}$ , $P_{OUT2}$ , $P_{OUT3}$ , $F=F1$ , $F2$ , $F3$ . Rotate 2:1 output VSWR through 360° phase. Post test $P_O$ = Pre test $P_O \pm 10\text{W}$ .
100%	Insertion Phase	IP	-20	20	DEG	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT3}$ , $F=F3$ . Measure at middle of pulse with respect to phase reference marked in groups of 5 degree margin.
BD	Pulse Risetime	RT	--	80	ns	$V_{CC}=V1$ , $PW=PW1$ , $DF=DF1$ , $T_F=25\pm5^\circ\text{C}$ , $P_{OUT}=P_{OUT1}$ , $P_{OUT2}$ , $P_{OUT3}$ , $F=F1$ , $F2$ , $F3$ .
Note	$V1 = 40\text{V}$ ; $PW1 = 100\mu\text{s}$ ; $DF1 = 10\%$ ; $P_{OUT1} = P_{OUT2} = P_{OUT3} = 300\text{W}$ ; $F1 = 1.215\text{ GHz}$ , $F2 = 1.300\text{ GHz}$ , $F3 = 1.400\text{ GHz}$ .					
Note	$T_F$ = Device flange temperature.					
Note	Screen 'BD' = parameter qualified By Design.					

**BROADBAND RF TEST FIXTURE IMPEDANCE CHARACTERISTICS**

Frequency (GHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
1.215	1.17-j2.27	1.42-j1.47
1.300	1.14-j1.77	1.4-j0.81
1.400	1.1-j1.24	1.4-j0.1
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



**RF TEST FIXTURE**

**PARTS LIST**

PC Board Type: ROGERS R03010 .025"  
Input PC Board Carrier: -03 (1.0")  
Output PC board Carrier: -03 (1.0")  
Transistor Carrier: -03 (P64)  
Transistor Clamp: -04 (P64)  
Heatsink: -10  
RF Connector: QS #2052-5636-02  
Chip Capacitor: ATC100A - 100pF, 2 plcs, C1, C2  
Electrolytic Capacitor, 68uf/63v, C3  
Dia wire  
Grounds: 4 places - \*  
Banana Jack Red - 1 place  
Banana Jack Black - 1 place

**ASSEMBLY AND PARTS LIST**

**DEFINITIONS**

<b>Data Sheet Status</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>Maximum Ratings</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

**WARNING**

<b>Product and environmental safety - toxic materials</b>
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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